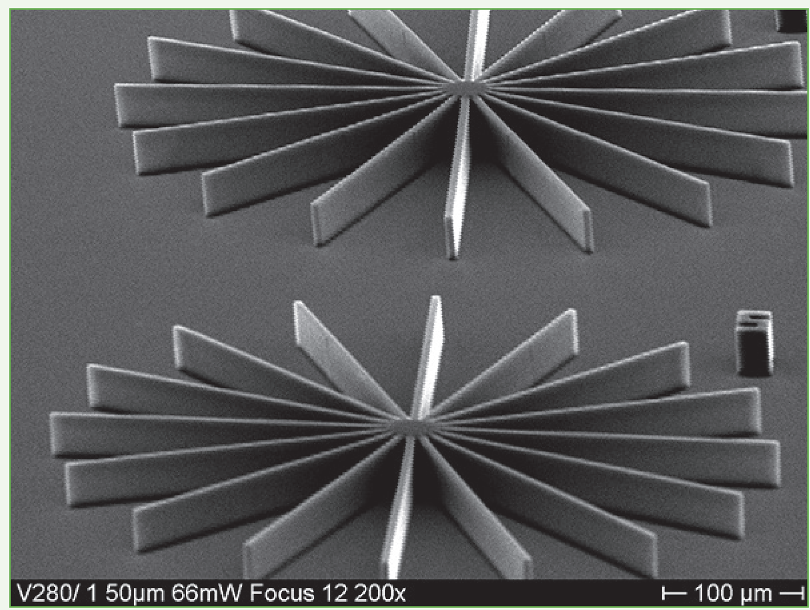
micro resist technology GmbH
Köpenicker Straße 325
12555 Berlin
Germany
Tel.: +49 (0) 30 641670100
Fax: +49 (0) 30 641670200
info@microresist.de
www.microresist.com

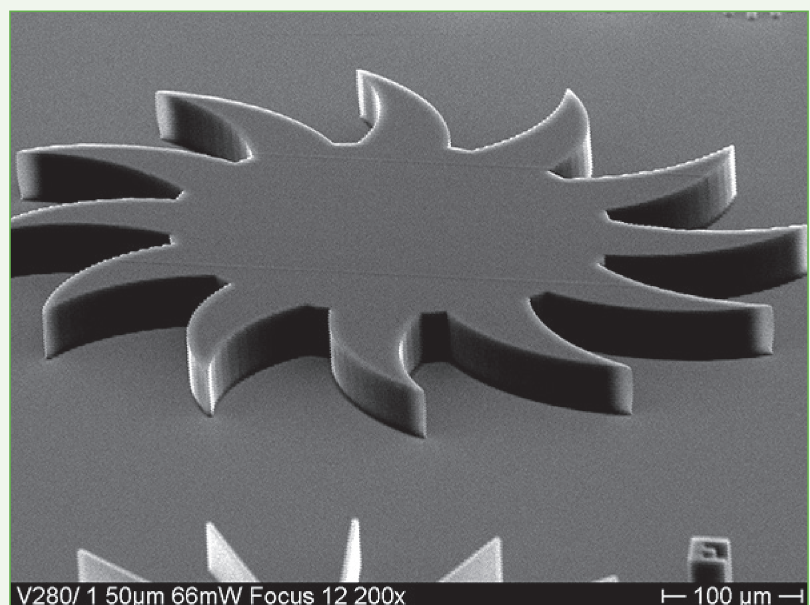
micro resist technology

mr-DWL — Negative Tone Photoresist Series

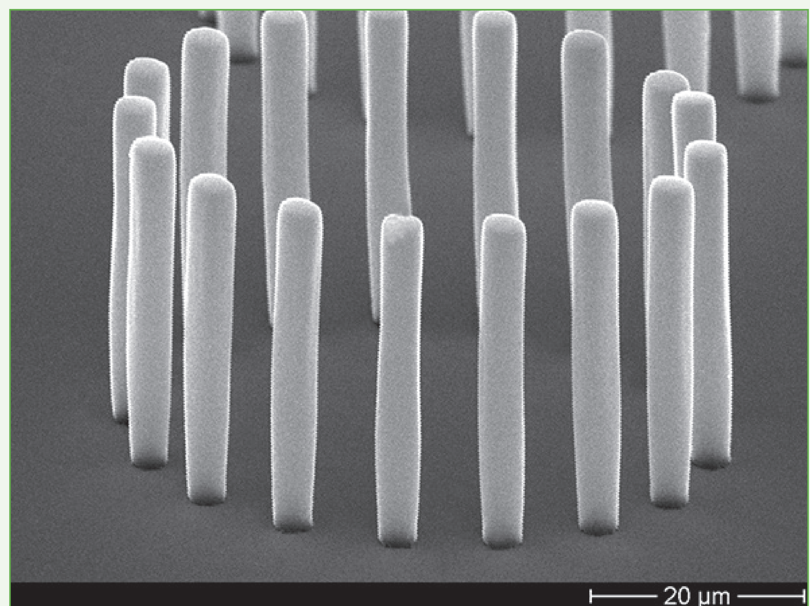
For direct writing laser @ 405 nm



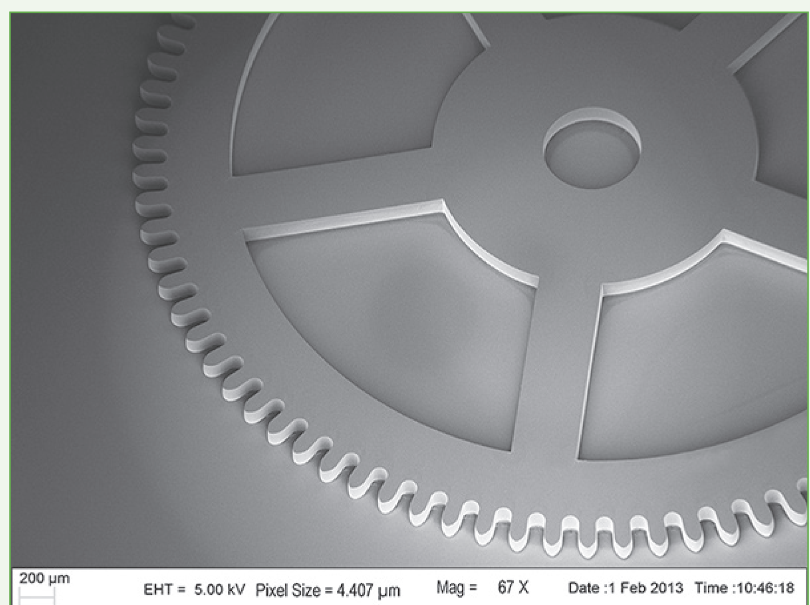
Film thickness 50 µm, 5 µm Star pattern, AR: 10

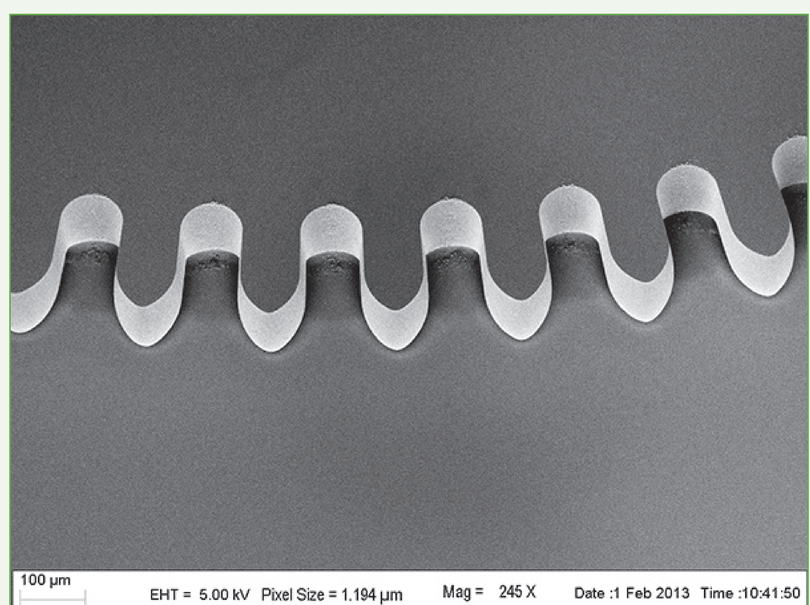


Film thickness 50 µm, wheel pattern



Film thickness 50 µm, 4 µm pillars, AR: 12.5


Film thickness 150 µm, gear-wheel


Film thickness 150 µm, gear-wheel, AR: 10

HEIDELBERG INSTRUMENTS

(Pictures – Courtesy of EPFL-LMIS 1, and Heidelberg Instruments)

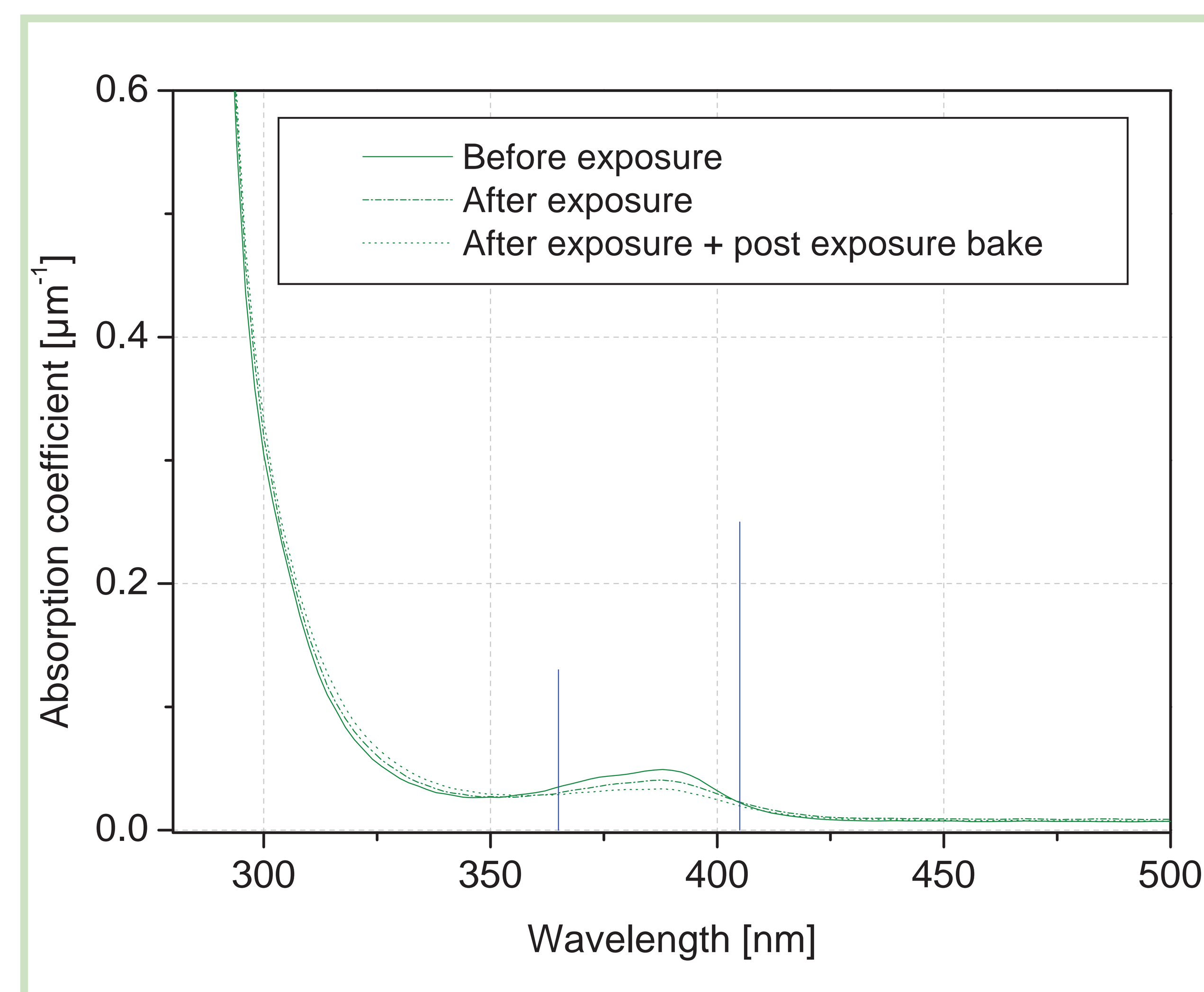
Resist patterning with direct writing laser @ 405 nm

Features:

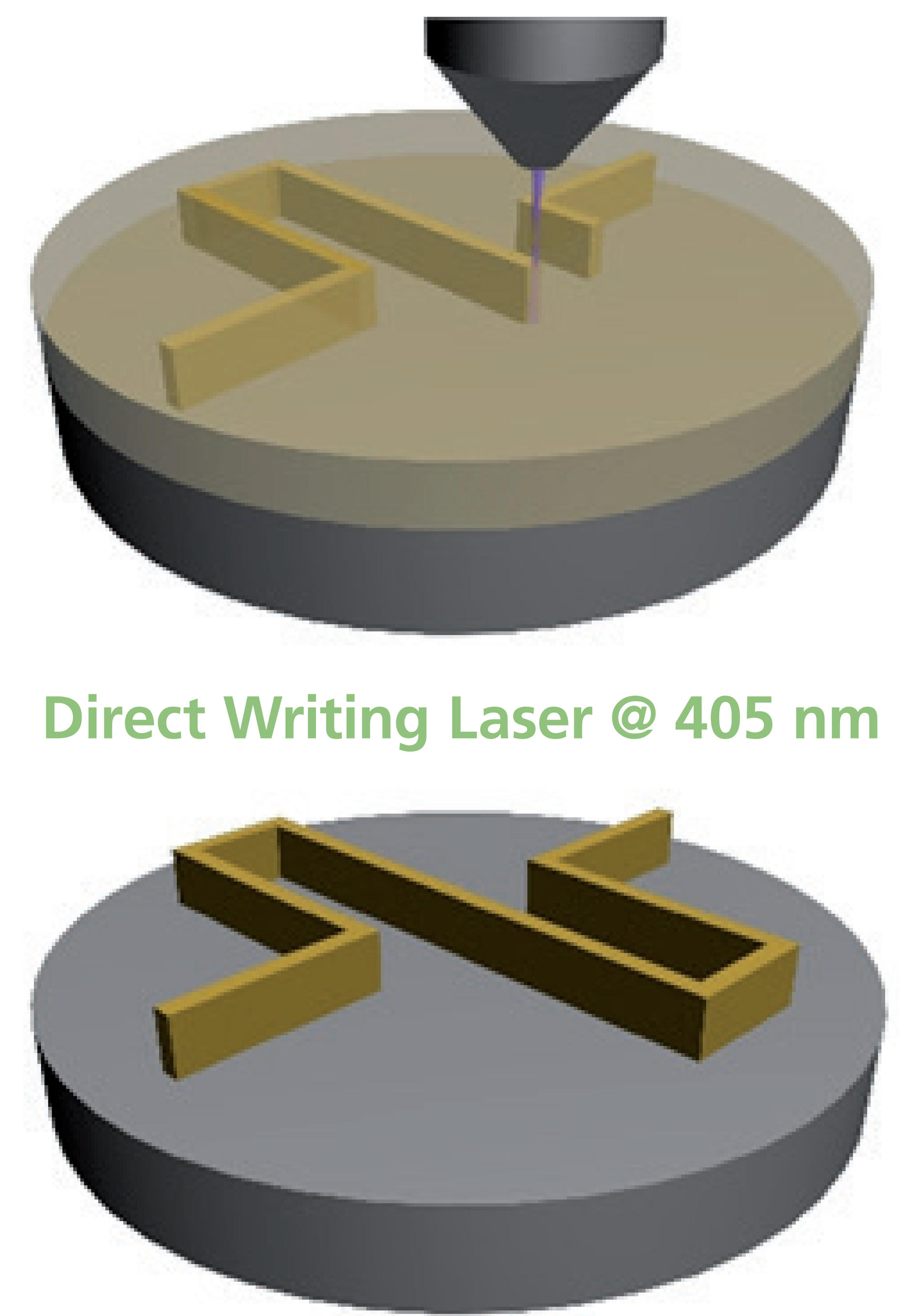
- Specifically designed for exposure wavelengths above 400 nm
- Direct Writing Laser @ 405 nm, e.g. Diode laser (DWL 66F5)
- High sensitivity
- Excellent thermal and chemical stability of the patterns
- High wet and dry etch stability

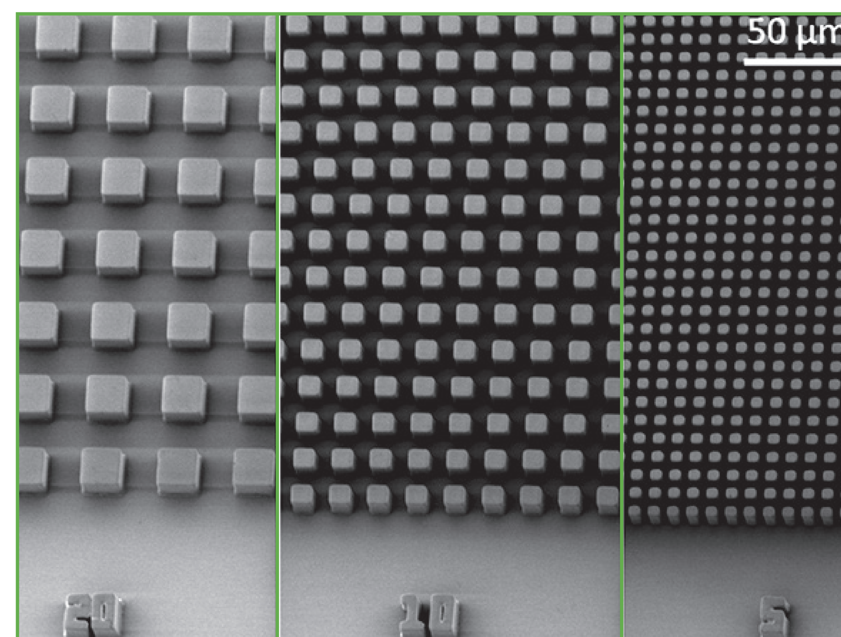
Technical data

Resist		mr-DWL 5	mr-DWL 40	mr-DWL 100
Film thickness	µm	3 - 12	20 - 100	20 - 150

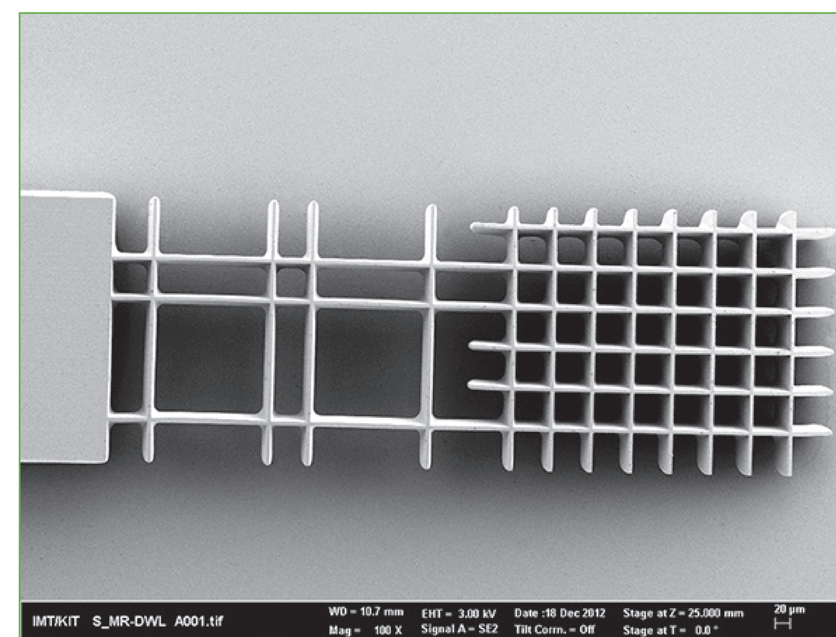


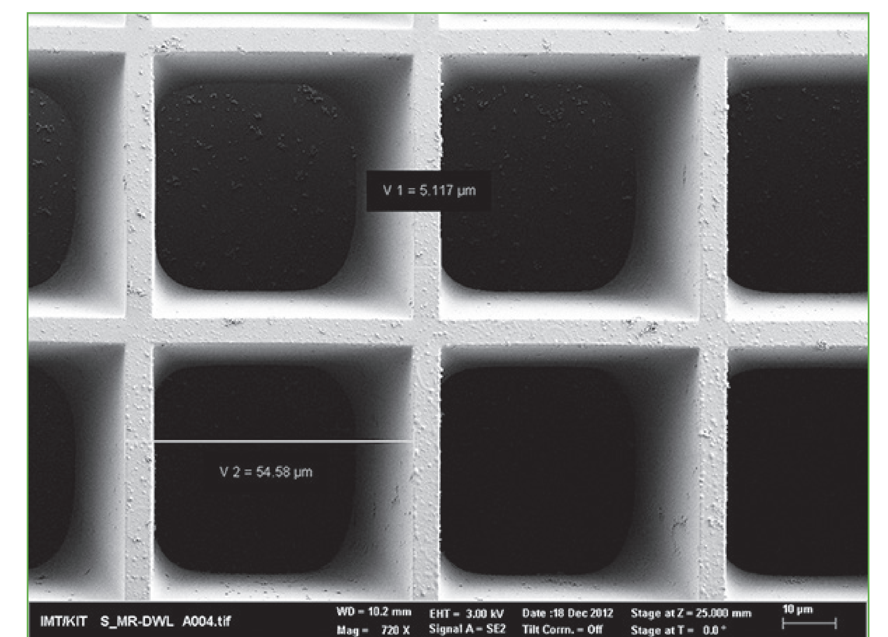
Process flow





Film thickness 20 µm


Film thickness 150 µm, AR: ≥ 10


Film thickness 150 µm, AR: ≥ 10

Applications:

- Fast and contactless prototyping by DWL
- Optical applications in micro systems technology
- Etch mask for wet and dry etch processes
- Mould for electroplating
- Mould for stamp fabrication by thermal or UV moulding

ls.16.02.17